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THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of )

Kichiya TANINO et al )

Appln. No.: 09/771,556 ) Art Unit: 1765

Filed: January 30, 2001 )

For: SINGLE CRYSTAL SiC AND A )  
METHOD OF GROWING THE SAME )

**RESPONSE TO NOTICE OF NON-COMPLIANT AMENDMENT (37 CFR 1.121)**

Honorable Commissioner of Patents and Trademarks  
Washington, D.C. 20231

Sir:

The following amendments to the specification are being submitted in response to  
the Notice of Non-Compliant Amendment (37 CFR 1.121) dated July 17, 2002.

**AMENDMENT**

**IN THE SPECIFICATION:**

Please replace pages 4-7 (first four lines only of page 7) with the following:

--used, although such single crystal SiC has many features more excellent than existing  
semiconductor materials such as Si and GaAs as described above.

**Summary of the Invention**

The invention has been conducted in view of the above-mentioned circumstances. It is an  
object of the invention to provide single crystal SiC of high quality to which influence of

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